



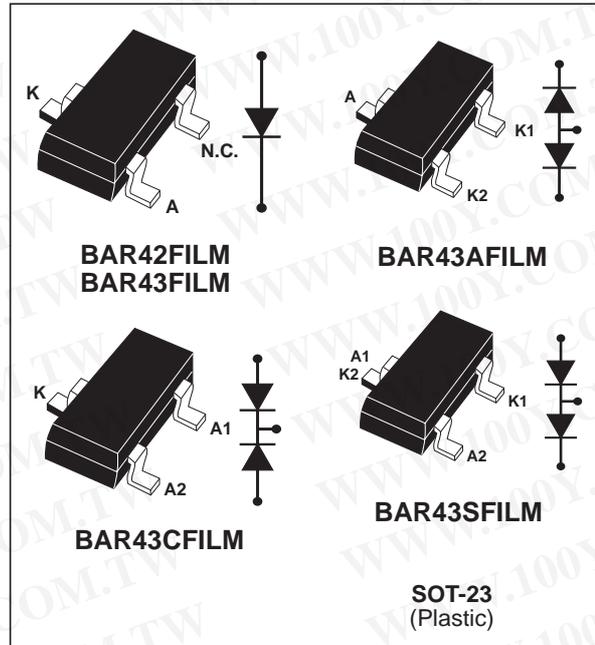
BAR42FILM BAR43/A/C/SFILM

SMALL SIGNAL SCHOTTKY DIODES

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)

DESCRIPTION

General purpose metal to silicon diodes featuring very low turn-on voltage and fast switching.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		30	V
I _F	Continuous forward current		100	mA
I _{FSM}	Surge non repetitive forward current	tp=10ms sinusoidal	750	mA
P _{tot}	Power dissipation (note 1)	T _{amb} = 25°C	250	mW
T _{stg}	Maximum storage temperature range		- 65 to +150	°C
T _j	Maximum operating junction temperature *		150	°C
T _L	Maximum temperature for soldering during 10s		260	°C

Note 1: for double diodes, P_{tot} is the total power dissipation of both diodes.

$$* : \frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}} \text{ thermal runaway condition for a diode on its own heatsink}$$

THERMAL RESISTANCE

Symbol	Test conditions	Value	Unit
R _{th(j-a)}	Junction-ambient *	500	°C/W

* Mounted on epoxy board with recommended pad layout.

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
V_{BR}	$T_j = 25^\circ C$	$I_R = 100\mu A$	30			V	
V_F^*	$T_j = 25^\circ C$	BAR 42FILM	$I_F = 10\text{ mA}$		0.35	0.4	V
			$I_F = 50\text{ mA}$		0.5	0.65	
		BAR 43FILM	$I_F = 2\text{ mA}$	0.26		0.33	
			$I_F = 15\text{ mA}$			0.45	
I_R^{**}	$T_j = 25^\circ C$	$V_R = 25V$			500	nA	
	$T_j = 100^\circ C$				100	μA	

Pulse test: * $t_p = 380\mu s, \delta < 2\%$
 ** $t_p = 5\text{ ms}, \delta < 2\%$

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	$T_j = 25^\circ C$	$V_R = 1V$ $F = 1\text{ MHz}$		7		pF
t_{rr}	$T_j = 25^\circ C$ $I_{rr} = 1\text{ mA}$	$I_F = 10\text{ mA}$ $R_L = 100\ \Omega$			5	ns
η^*	$T_j = 25^\circ C$ $F = 45\text{ MHz}$	$R_L = 50\text{ K}\Omega$ $V_i = 2V$	80			%

* Detection efficiency

Fig. 1-1: Forward voltage drop versus forward current (typical values, low level).

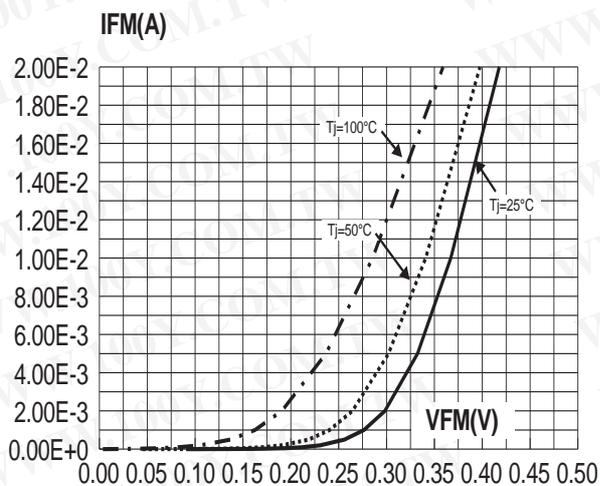


Fig. 1-2: Forward voltage drop versus forward current (typical values, high level).

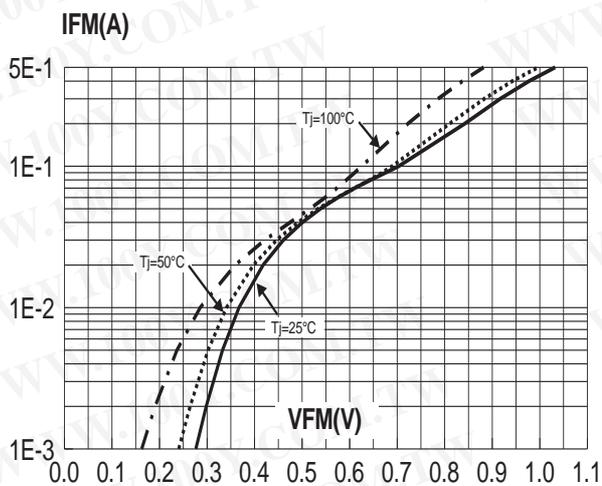


Fig. 2: Reverse leakage current versus reverse voltage applied (typical values).

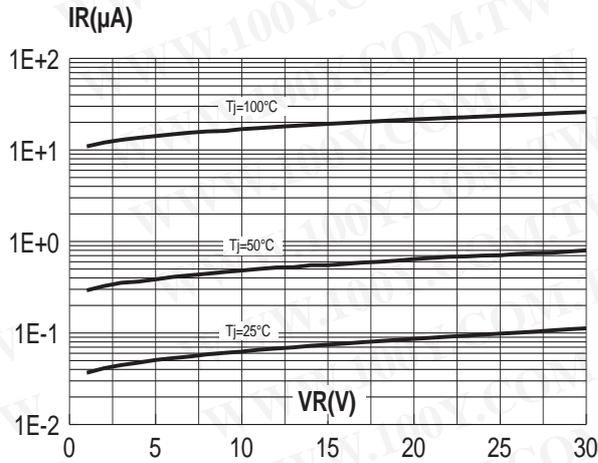


Fig. 3: Reverse leakage current versus junction temperature.

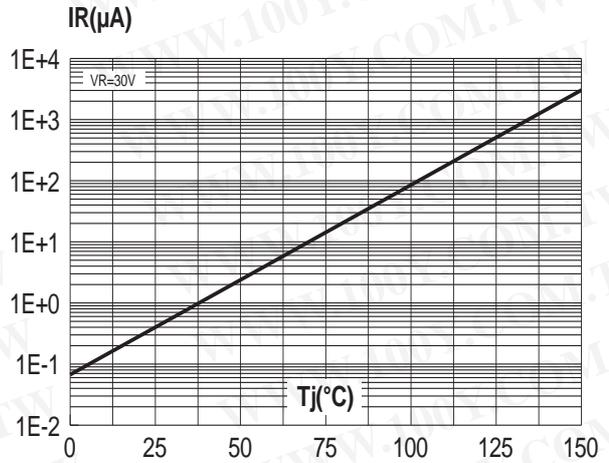


Fig. 4: Junction capacitance versus reverse voltage applied (typical values).

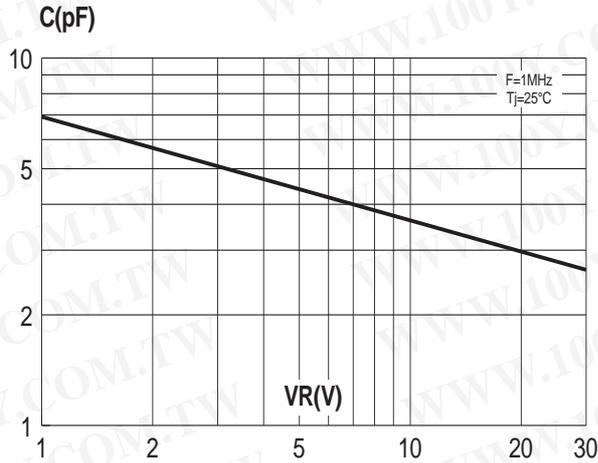


Fig. 5: Relative variation of thermal impedance junction to ambient versus pulse duration (epoxy FR4 with recommended pad layout, $e(Cu) = 35\mu m$).

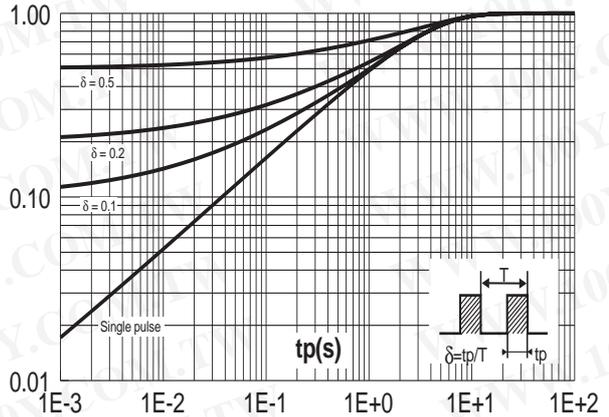
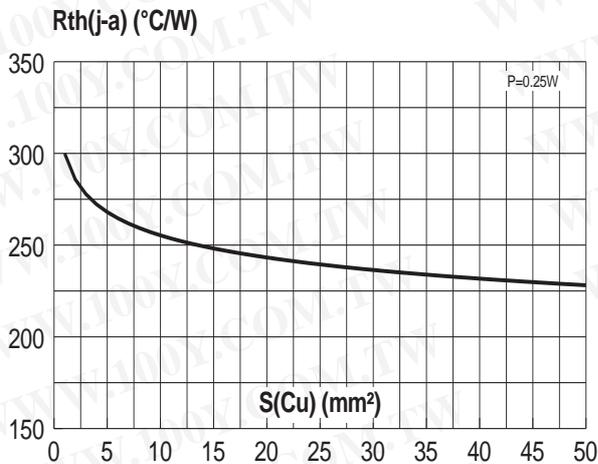


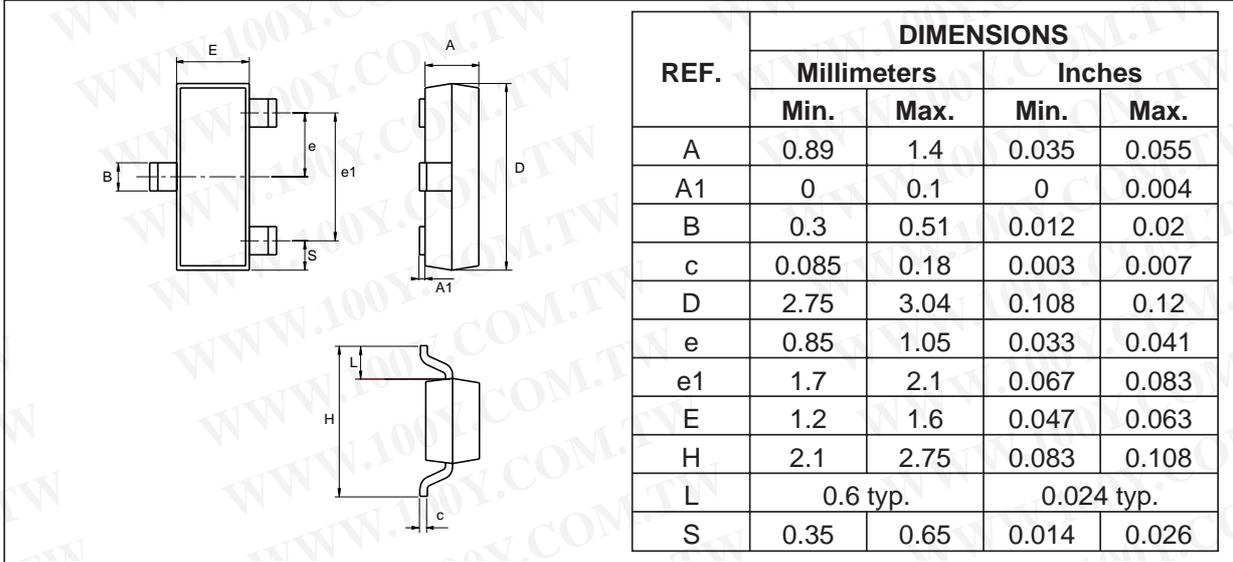
Fig. 6: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness: $35\mu m$).



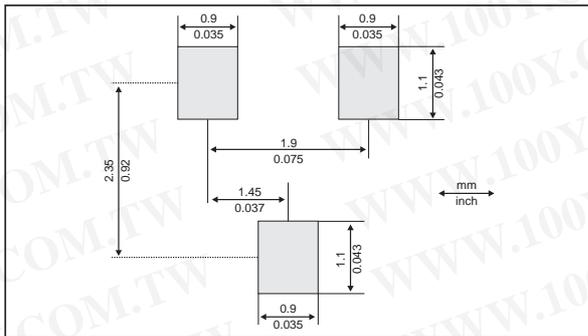
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BAR42FILM BAR43/A/C/SFILM

PACKAGE MECHANICAL DATA SOT-23 (Plastic)



FOOT PRINT DIMENSIONS



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Ordering type	Marking	Package	Weight	Base qty	Delivery mode
BAR42FILM	D94	SOT-23	0.01g	3000	Tape & reel
BAR43FILM	D95	SOT-23	0.01g	3000	Tape & reel
BAR43AFILM	DB1	SOT-23	0.01g	3000	Tape & reel
BAR43CFILM	DB2	SOT-23	0.01g	3000	Tape & reel
BAR43SFILM	DA5	SOT-23	0.01g	3000	Tape & reel

Epoxy meets UL94,V0

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